BC212, BC212B, BC213, BC214

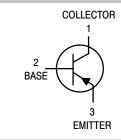
Amplifier Transistors

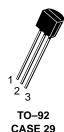
PNP Silicon



ON Semiconductor[™]

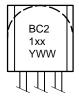
http://onsemi.com





CASE 29 STYLE 17

MARKING DIAGRAMS



ORDERING INFORMATION

Device	Package	Shipping
BC212	TO-92	5000 Units/Box
BC212B	TO-92	5000 Units/Box
BC212BRL1	TO-92	2000/Tape & Reel
BC212BZL1	TO-92	2000/Ammo Pack
BC213	TO-92	5000 Units/Box
BC214	TO-92	5000 Units/Box
BC214RL1	TO-92	2000/Tape & Reel

MAXIMUM RATINGS

			1
Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC212 BC213 BC214	V _{CEO}	-50 -30 -30	Vdc
Collector-Base Voltage BC212 BC213 BC214	V _{CBO}	-60 -45 -45	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ι _C	-100	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	350 2.8	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.0 8.0	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	357	°C/W
Thermal Resistance, Junction to Case	$R_{ extsf{ heta}JC}$	125	°C/W

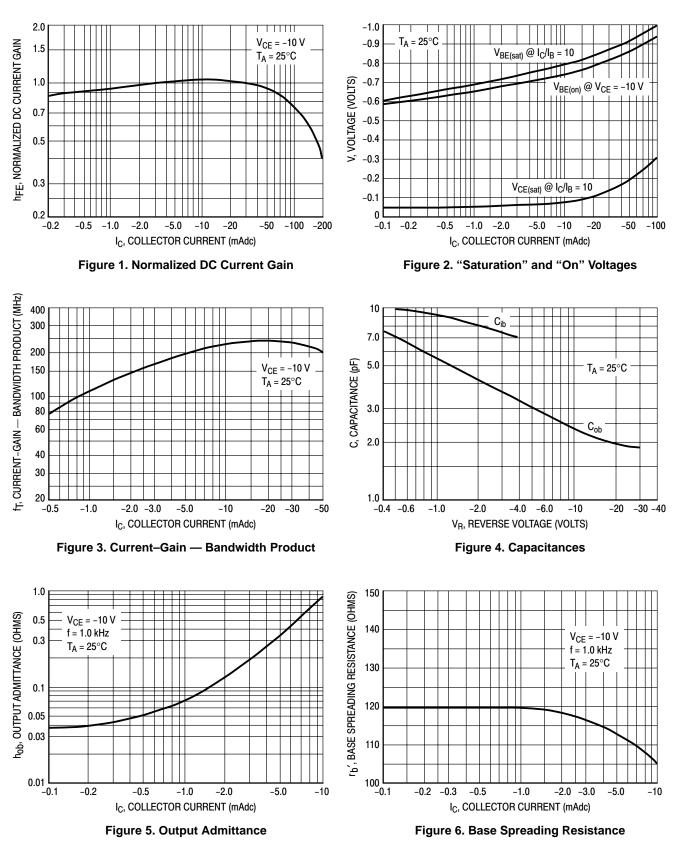
BC212, BC212B, BC213, BC214

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Collector–Emitter Breakdown Voltage ($I_C = -2.0 \text{ mAdc}, I_B = 0$)	BC212 BC213 BC214	V _{(BR)CEO}	50 30 30	_ _ _	_ _ _	Vdc
Collector–Base Breakdown Voltage ($I_C = -10 \ \mu A, I_E = 0$)	BC212 BC213 BC214	V _{(BR)CBO}	60 45 45		- - -	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10 \ \mu Adc, I_C = 0$)	BC212 BC213 BC214	V _{(BR)EBO}	-5 -5 -5	- - -	_ _ _	Vdc
Collector–Emitter Leakage Current $(V_{CB} = -30 \text{ V})$	BC212 BC213 BC214	I _{CBO}	- - -	- - -	-15 -15 -15	nAdc
Emitter–Base Leakage Current $(V_{EB} = -4.0 \text{ V}, I_C = 0)$	BC212 BC213 BC214	I _{EBO}	- - -	- - -	-15 -15 -15	nAdc
ON CHARACTERISTICS						
DC Current Gain (I _C = -10μ Adc, V _{CE} = -5.0 Vdc)	BC212 BC213 BC214	h _{FE}	40 40 100	- - -		_
$(I_{C} = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	BC212 BC213 BC214		60 80 140	- - -	_ _ 600	
$(I_{C} = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$ (Note 1.)	BC212, BC214 BC213			120 140		
Collector–Emitter Saturation Voltage ($I_C = -10$ mAdc, $I_B = -0.5$ mAdc) ($I_C = -100$ mAdc, $I_B = -5.0$ mAdc) (Note 1.)		V _{CE(sat)}		-0.10 -0.25	_ _0.6	Vdc
Base–Emitter Saturation Voltage ($I_C = -100 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$)		V _{BE(sat)}	-	-1.0	-1.4	Vdc
Base–Emitter On Voltage ($I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}$)		V _{BE(on)}	-0.6	-0.62	-0.72	Vdc
DYNAMIC CHARACTERISTICS				•		•
Current–Gain – Bandwidth Product ($I_C = -10$ mAdc, $V_{CE} = -5.0$ Vdc, f = 100 MHz)	BC212 BC214 BC213	fT	_ _ _	280 320 360	_ _ _	MHz
Common–Base Output Capacitance $(V_{CB} = -10 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$		C _{ob}	_	_	6.0	pF
Noise Figure $(I_C = -0.2 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}, R_S = 2.0 \text{ k}\Omega, f = 1.0 \text{ kHz})$ $(I_C = -0.2 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}, R_S = 2.0 \text{ k}\Omega, f = 1.0 \text{ kHz}, f = 200 \text{ Hz})$	BC214 BC212, BC213	NF		-	2 10	dB
Small–Signal Current Gain ($I_C = -2.0$ mAdc, $V_{CE} = -5.0$ Vdc, f = 1.0 kHz)	BC212 BC213 BC214 BC212B	h _{fe}	60 80 140 200	- - - -	- - - 400	-

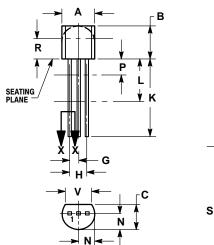
1. Pulse Test: Tp 300 s, Duty Cycle 2.0%.

BC212, BC212B, BC213, BC214



PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**





NOTES:

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

CONTROLLING DIMENSION: INCH. CONTOUR OF PACKAGE BEYOND DIMENSION R 2. 3. IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND

4 BEYOND DIMENSION K MINIMUM

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER

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